formed in the photosensitive resin, and smooth concave and convex portions are provided on an upper surface of the resin. A film including molybdenum nitride (MoN) and a reflective pixel electrode film are successively laminated on the photosensitive resin. The nitrogen content in the MoN film may be between 5 atomic % and 30 atomic % inclusive so that the MoN film can obtain strong adhesion to the photosensitive resin and prevent or reduce decrease in the etching rate of the MoN film.

BI Cont

IN THE CLAIMS

Please cancel claim 6.

Please substitute the following amended claim(s) for corresponding claim(s) previously presented. A copy of the amended claim(s) showing current revisions is attached.

1. (Amended) A liquid crystal display (LCD) comprising:

at least one thin film transistor (TFT), an interlayer insulator, and at least one reflective pixel electrode defining at least part of a pixel of the LCD and being supported by a substrate, wherein the interlayer insulator is located at least partially between the reflective pixel electrode and the substrate, and

a film comprising molybdenum nitride formed immediately below and in contact with the reflective pixel electrode, and above and contacting the interlayer insulator, so that the film comprising molybdenum nitride is at least partially located between and contacting each of the reflective pixel electrode and the interlayer insulator.

2. (Amended) The LCD according to claim 1, wherein the reflective pixel electrode comprises aluminum (Al)

3. (Amended) The LCD according to claim 1, wherein the film comprising molybdenum nitride has a nitrogen content between 5 atomic % and 30 atomic %.

4. (Amended) The LCD according to claim 1, wherein the interlayer insulator comprises a photosensitive resin.

5. (Amended) The LCD according to claim 1, wherein the insulating film comprises a polymeric resin.

7. (Amended) A liquid crystal display comprising:

a pair of substrates,

a liquid crystal layer between the pair of substrates,

a laminated layer provided on at least one of the substrates, wherein the laminated layer comprises an insulating film and a film comprising molybdenum nitride laminated to and over at least part of the insulating film, so that the film comprising molybdenum nitride contacts the insulating film,

wherein the insulating layer is located at least partially over address lines of the liquid crystal display; and

500

a reflective metal film having a light reflecting function and provided in at least one pixel region of the display for contributing to displaying of images in the display, wherein the reflective metal film is formed on the laminated layer so as to contact the film comprising molybdenum nitride.

- 8. (Amended) The liquid crystal display according to claim 7, wherein the film comprising molybdenum nitride has a nitrogen content between 5 atomic % and 30 atomic %.
- 9. (Amended) The liquid crystal display according to claim 7, wherein the reflective metal film is a pixel electrode for applying a voltage to the liquid crystal layer.
- 10. (Amended) The liquid crystal display according to claim 7, further comprising an electrode comprising indium-tin oxide (ITO) formed on the same substrate on which the reflective metal film is formed, wherein the film comprising molybdenum nitride is provided at least partially between the reflective metal film and the electrode comprising ITO.

Please add the following new claims:

3

11. (New) A liquid crystal display (LCD) comprising:

at least one thin film transistor (TFT),

an insulating layer at least partially provided over address lines of the LCD, at least some of said address lines being in communication with the TFT;

at least one reflective pixel electrode defining at least part of a pixel of the LCD; and

a film comprising molybdenum in direct contact with the under-side of said reflective pixel electrode, so that the film comprising molybdenum is in directly contact with the under-side of the reflective pixel electrode and an upper surface of the insulating layer.

12. (New) An electronic device comprising:

a substrate supporting an insulating layer and a conductive electrode layer; and a layer comprising molybdenum nitride located between and contacting each of the insulating layer and the conductive electrode layer, wherein the layer comprising molybdenum nitride is located below the conductive electrode layer and above the insulating layer so that the insulating layer is between the substrate and the layer comprising molybdenum nitride.

13. (New) The electronic device of claim 12, further comprising a plurality of TFTs on the substrate, wherein the insulating layer is formed at least partially over the TFTs.

TFTs